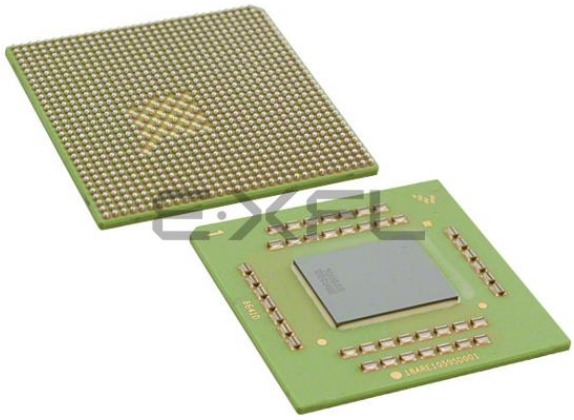

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e600
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	994-BCBGA, FCCBGA
Supplier Device Package	994-FCCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc8641thx1000nc

  - Support for PCI-Express message-shared interrupts (MSIs)
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data operating at up to 133 MHz
  - Eight chip selects support eight external slaves
- Integrated DMA controller
  - Four-channel controller
  - All channels accessible by both the local and the remote masters
  - Supports transfers to or from any local memory or I/O port
  - Ability to start and flow control each DMA channel from external 3-pin interface
- Device performance monitor
  - Supports eight 32-bit counters that count the occurrence of selected events
  - Ability to count up to 512 counter-specific events
  - Supports 64 reference events that can be counted on any of the 8 counters
  - Supports duration and quantity threshold counting
  - Burstiness feature that permits counting of burst events with a programmable time between bursts
  - Triggering and chaining capability
  - Ability to generate an interrupt on overflow
- Dual I^2C controllers
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
  - Programming model compatible with the original 16450 UART and the PC16550D
- IEEE 1149.1-compatible, JTAG boundary scan
- Available as 1023 pin Hi-CTE flip chip ceramic ball grid array (FC-CBGA)

NOTE

There is no required order sequence between the individual rails for this item (# 1). However, V_{DD}_PLAT, AV_{DD}_PLAT rails must reach 90% of their recommended value before the rail for Dn_GV_{DD}, and Dn_MV_{REF} (in next step) reaches 10% of their recommended value. AV_{DD} type supplies must be delayed with respect to their source supplies by the RC time constant of the PLL filter circuit described in Section 20.2.1, "PLL Power Supply Filtering."

2. D*n*_GV_{DD}, D*n*_MV_{REF}

NOTE

It is possible to leave the related power supply (D*n*_GV_{DD}, D*n*_MV_{REF}) turned off at reset for a DDR port that will not be used. Note that these power supplies can only be powered up again at reset for functionality to occur on the DDR port.

3. SYSCLK

The recommended order of power down is as follows:

1. D*n*_GV_{DD}, D*n*_MV_{REF}
2. All power rails other than DDR I/O (D*n*_GV_{DD}, D*n*_MV_{REF}).

NOTE

SYSCLK may be powered down simultaneous to either of item # 1 or # 2 in the power down sequence. Beyond this, the power supplies may power down simultaneously if the preservation of DDR*n* memory is not a concern.

See Figure 3 for more details on the Power and Reset Sequencing details.

Table 29. GMII Receive AC Timing Specifications (continued)

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5% and 2.5 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock fall time (80%-20%)	t_{GRXF}[2]	—	—	1.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.
3. ±100 ppm tolerance on RX_CLK frequency

Figure 11 provides the AC test load for eTSEC.

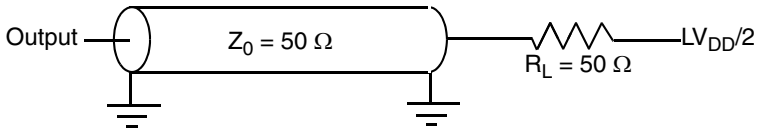

Figure 11. eTSEC AC Test Load

Figure 12 shows the GMII receive AC timing diagram.

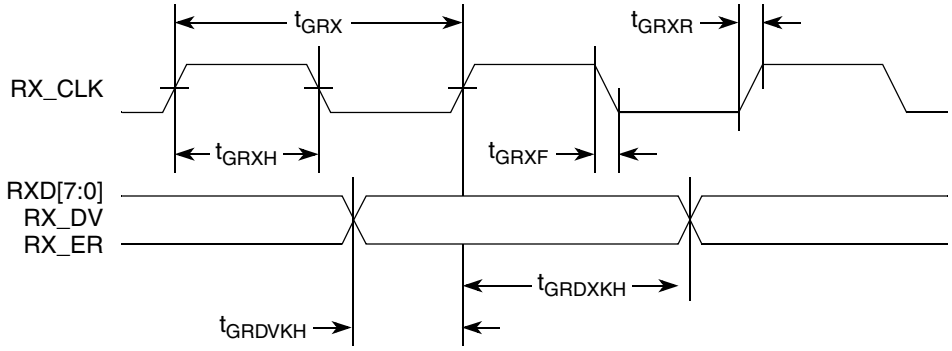

Figure 12. GMII Receive AC Timing Diagram

8.2.3.2 MII Receive AC Timing Specifications

Table 31 provides the MII receive AC timing specifications.

Table 31. MII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}[2,3]	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}[3]	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise time (20%-80%)	t_{MRXR}[2]	1.0	—	4.0	ns
RX_CLK clock fall time (80%-20%)	t_{MRXF}[2]	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.
3. ±100 ppm tolerance on RX_CLK frequency

Figure 14 provides the AC test load for eTSEC.

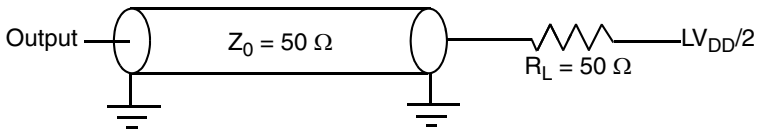

Figure 14. eTSEC AC Test Load

Figure 15 shows the MII receive AC timing diagram.

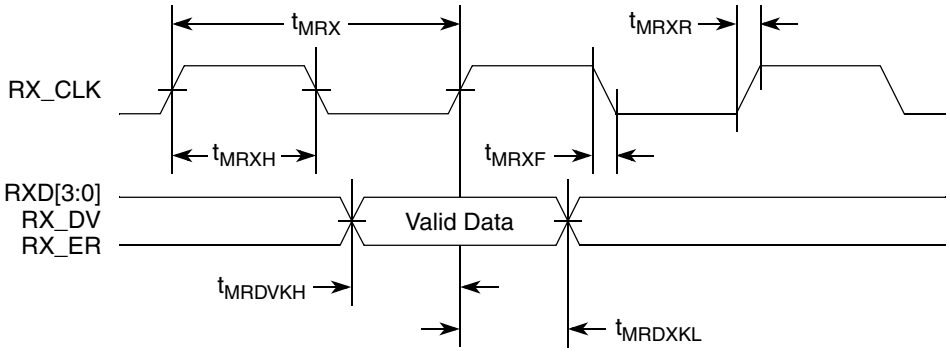

Figure 15. MII Receive AC Timing Diagram

Table 39. MII Management AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} is 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit	Notes
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	4
MDC fall time	t_{MDHF}	—	—	10	ns	4

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the system clock speed. (The maximum frequency is the maximum platform frequency divided by 64.)
3. This parameter is dependent on the system clock speed. (That is, for a system clock of 267 MHz, the maximum frequency is 8.3 MHz and the minimum frequency is 1.2 MHz; for a system clock of 375 MHz, the maximum frequency is 11.7 MHz and the minimum frequency is 1.7 MHz.)
4. Guaranteed by design.
5. t_{MPXCLK} is the platform (MPX) clock

Figure 23 provides the AC test load for eTSEC.

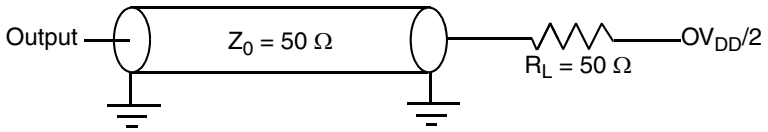

Figure 23. eTSEC AC Test Load

NOTE

Output will see a 50-Ω load since what it sees is the transmission line.

Figure 24 shows the MII management AC timing diagram.

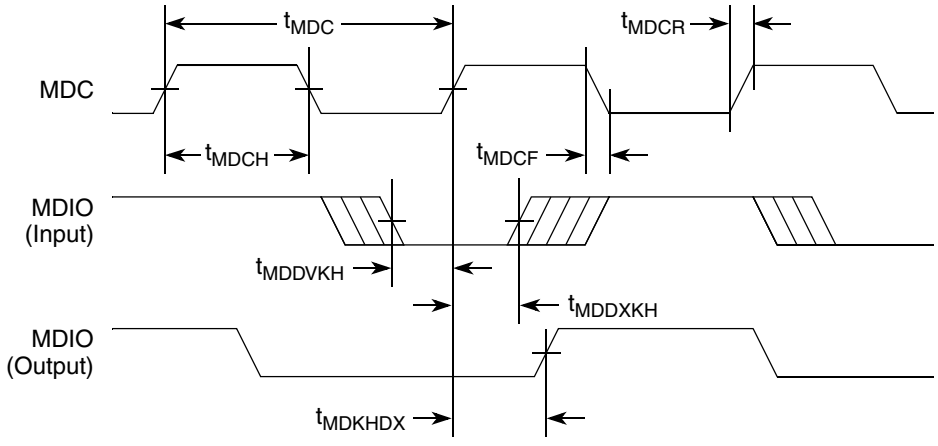

Figure 24. MII Management Interface Timing Diagram

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8641.

10.1 Local Bus DC Electrical Characteristics

Table 40 provides the DC electrical characteristics for the local bus interface operating at OV_{DD} = 3.3 V DC.

Table 40. Local Bus DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN} [1] = 0 V or V_{IN} = OV_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.2	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

10.2 Local Bus AC Electrical Specifications

Table 41 describes the timing parameters of the local bus interface at OV_{DD} = 3.3 V with PLL enabled. For information about the frequency range of local bus see Section 18.1, "Clock Ranges."

Table 41. Local Bus Timing Parameters (OV_{DD} = 3.3 V)m - PLL Enabled

Parameter	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	—	ns	2
Local Bus Duty Cycle	t_{LBKH}/t_{LBK}	45	55	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIVKH1}$	1.8	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.7	—	ns	3, 4
Input hold from local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.0	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.2	ns	—
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.3	ns	—

Table 44. JTAG AC Timing Specifications (Independent of SYSCLK) [1] (continued)

At recommended operating conditions (see Table 3).

Parameter	Symbol [2]	Min	Max	Unit	Notes
Output hold times: Boundary-scan data TDO	 t_{JTKLDX} t_{JTKLOX}	 30 30	 — —	ns	5, 6
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 3 3	 19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 32). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design.

Figure 32 provides the AC test load for TDO and the boundary-scan outputs.

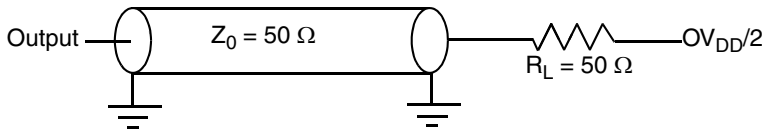

Figure 32. AC Test Load for the JTAG Interface

Figure 33 provides the JTAG clock input timing diagram.

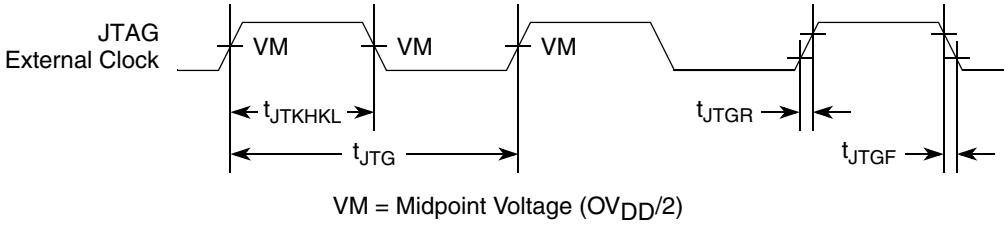

Figure 33. JTAG Clock Input Timing Diagram

MPC8641D SerDes reference clock input's DC requirement, AC-coupling has to be used. Figure 45 assumes that the LVPECL clock driver's output impedance is 50 Ω. R1 is used to DC-bias the LVPECL outputs prior to AC-coupling. Its value could be ranged from 140 Ω to 240 Ω depending on clock driver vendor's requirement. R2 is used together with the SerDes reference clock receiver's 50-Ω termination resistor to attenuate the LVPECL output's differential peak level such that it meets the MPC8641D SerDes reference clock's differential input amplitude requirement (between 200 mV and 800 mV differential peak). For example, if the LVPECL output's differential peak is 900 mV and the desired SerDes reference clock input amplitude is selected as 600mV, the attenuation factor is 0.67, which requires R2 = 25 Ω. Please consult clock driver chip manufacturer to verify whether this connection scheme is compatible with a particular clock driver chip.

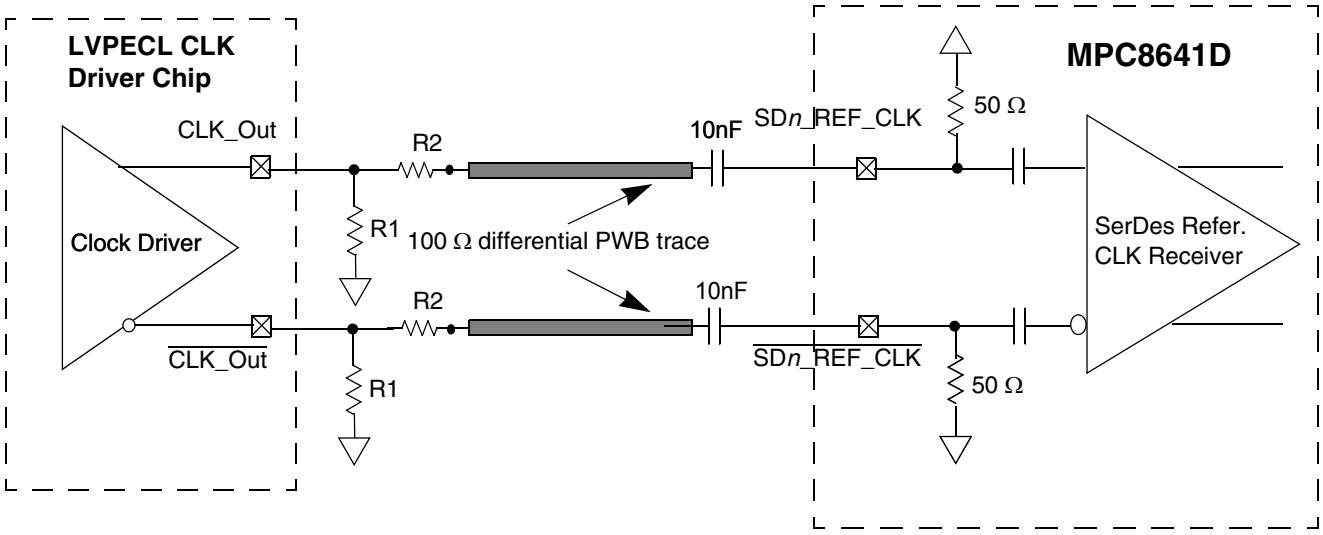

Figure 45. AC-Coupled Differential Connection with LVPECL Clock Driver (Reference Only)

Table 51. SD*n*_REF_CLK and $\overline{\text{SD}n\text{\_REF\_CLK}}$ AC Requirements

Symbol	Parameter Description	Min	Typical	Max	Units	Comments
t_{REF}	REFCLK cycle time	—	10(8)	—	ns	8 ns applies only to serial RapidIO with 125-MHz reference clock
t_{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles	—	—	80	ps	—
t_{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location	–40	—	40	ps	—

15.3 Signal Definitions

LP-Serial links use differential signaling. This section defines terms used in the description and specification of differential signals. Figure 53 shows how the signals are defined. The figures show waveforms for either a transmitter output (TD and $\overline{\text{TD}}$) or a receiver input (RD and $\overline{\text{RD}}$). Each signal swings between A Volts and B Volts where A > B. Using these waveforms, the definitions are as follows:

1. The transmitter output signals and the receiver input signals TD, $\overline{\text{TD}}$, RD and $\overline{\text{RD}}$ each have a peak-to-peak swing of A – B Volts
2. The differential output signal of the transmitter, V_{OD}, is defined as $V_{TD}–V_{\overline{TD}}$
3. The differential input signal of the receiver, V_{ID}, is defined as $V_{RD}–V_{\overline{RD}}$
4. The differential output signal of the transmitter and the differential input signal of the receiver each range from A – B to –(A – B) Volts
5. The peak value of the differential transmitter output signal and the differential receiver input signal is A – B Volts
6. The peak-to-peak value of the differential transmitter output signal and the differential receiver input signal is 2 * (A – B) Volts

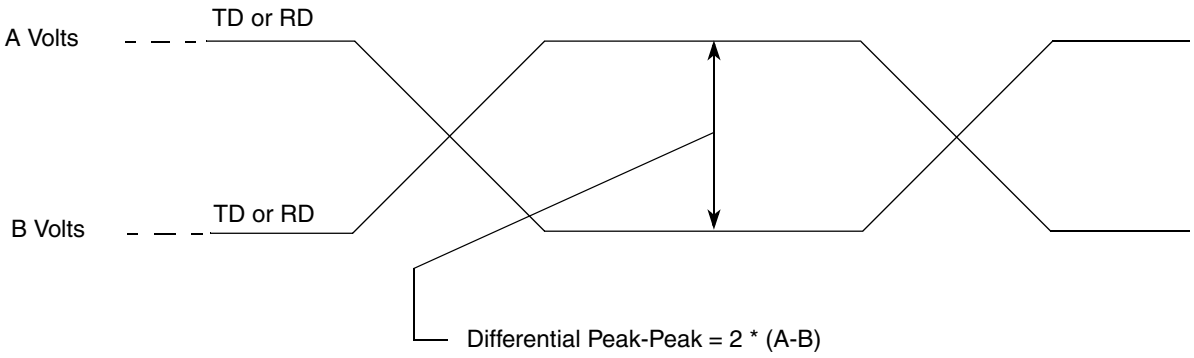

Figure 53. Differential Peak-Peak Voltage of Transmitter or Receiver

To illustrate these definitions using real values, consider the case of a CML (Current Mode Logic) transmitter that has a common mode voltage of 2.25 V and each of its outputs, TD and $\overline{\text{TD}}$, has a swing that goes between 2.5V and 2.0V. Using these values, the peak-to-peak voltage swing of the signals TD and $\overline{\text{TD}}$ is 500 mV p-p. The differential output signal ranges between 500 mV and –500 mV. The peak differential voltage is 500 mV. The peak-to-peak differential voltage is 1000 mV p-p.

Table 60. Receiver AC Timing Specifications—2.5 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential Input Voltage	V_{IN}	200	1600	mV p-p	Measured at receiver
Deterministic Jitter Tolerance	J_D	0.37	—	UI p-p	Measured at receiver
Combined Deterministic and Random Jitter Tolerance	J_{DR}	0.55	—	UI p-p	Measured at receiver
Total Jitter Tolerance[1]	J_T	0.65	—	UI p-p	Measured at receiver
Multiple Input Skew	S_{MI}	—	24	ns	Skew at the receiver input between lanes of a multilane link
Bit Error Rate	BER	—	10^{-12}	—	—
Unit Interval	UI	400	400	ps	+/– 100 ppm

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of Figure 55. The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk and other variable system effects.

Table 61. Receiver AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential Input Voltage	V_{IN}	200	1600	mV p-p	Measured at receiver
Deterministic Jitter Tolerance	J_D	0.37	—	UI p-p	Measured at receiver
Combined Deterministic and Random Jitter Tolerance	J_{DR}	0.55	—	UI p-p	Measured at receiver
Total Jitter Tolerance[1]	J_T	0.65	—	UI p-p	Measured at receiver
Multiple Input Skew	S_{MI}	—	22	ns	Skew at the receiver input between lanes of a multilane link
Bit Error Rate	BER	—	10^{-12}	—	—
Unit Interval	UI	320	320	ps	+/– 100 ppm

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of Figure 55. The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk and other variable system effects.

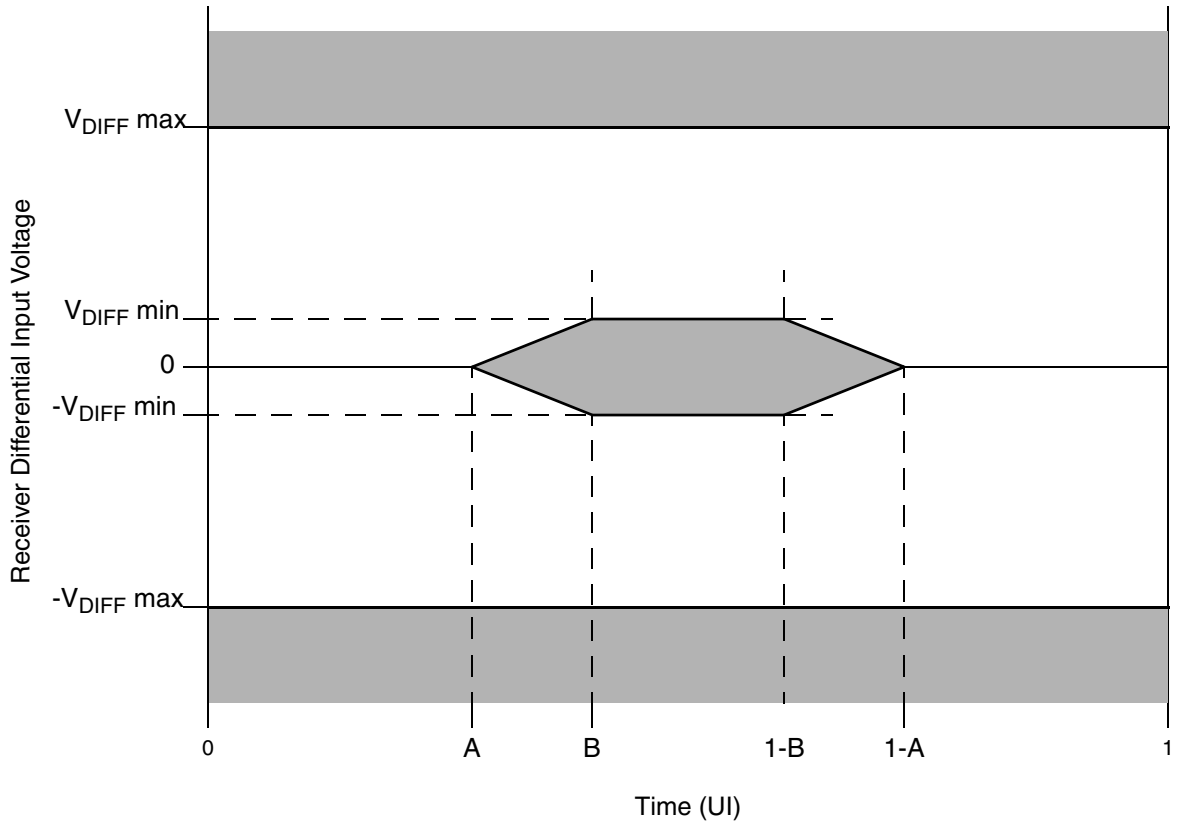

Figure 56. Receiver Input Compliance Mask

Table 62. Receiver Input Compliance Mask Parameters Exclusive of Sinusoidal Jitter

Receiver Type	V_{DIFF}min (mV)	V_{DIFF}max (mV)	A (UI)	B (UI)
1.25 GBaud	100	800	0.275	0.400
2.5 GBaud	100	800	0.275	0.400
3.125 GBaud	100	800	0.275	0.400

15.9 Measurement and Test Requirements

Since the LP-Serial electrical specification are guided by the XAUI electrical interface specified in Clause 47 of IEEE 802.3ae-2002, the measurement and test requirements defined here are similarly guided by Clause 47. In addition, the CJPAT test pattern defined in Annex 48A of IEEE 802.3ae-2002 is specified as the test pattern for use in eye pattern and jitter measurements. Annex 48B of IEEE 802.3ae-2002 is recommended as a reference for additional information on jitter test methods.

15.9.1 Eye Template Measurements

For the purpose of eye template measurements, the effects of a single-pole high pass filter with a 3 dB point at (Baud Frequency)/1667 is applied to the jitter. The data pattern for template measurements is the

16 Package

This section details package parameters and dimensions.

16.1 Package Parameters for the MPC8641

The package parameters are as provided in the following list. The package type is 33 mm × 33 mm, 1023 pins. There are two package options: high-lead Flip Chip-Ceramic Ball Grid Array (FC-CBGA), and lead-free (FC-CBGA).

For all package types:

Die size	12.1 mm × 14.7 mm
Package outline	33 mm × 33 mm
Interconnects	1023
Pitch	1 mm
Total Capacitor count	43 caps; 100 nF each

For high-lead FC-CBGA (package option: HCTE[1] HX)

Maximum module height	2.97 mm
Minimum module height	2.47 mm
Solder Balls	89.5% Pb 10.5% Sn
Ball diameter (typical[2])	0.60 mm

For RoHS lead-free FC-CBGA (package option: HCTE[1] VU) and lead-free FC-CBGA (package option: HCTE[1] VJ)

Maximum module height	2.77 mm
Minimum module height	2.27 mm
Solder Balls	95.5% Sn 4.0% Ag 0.5% Cu
Ball diameter (typical[2])	0.60 mm

[1] High-coefficient of thermal expansion

[2] Typical ball diameter is before reflow

8. Note that for MPC8641 (single core) the solder balls for the following signals/pins are not populated in the package: VDD_Core1 (R16, R18, R20, T17, T19, T21, T23, U16, U18, U22, V17, V19, V21, V23, W16, W18, W20, W22, Y17, Y19, Y21, Y23, AA16, AA18, AA20, AA22, AB23, AC24) and SENSEVDD_Core1 (U20).

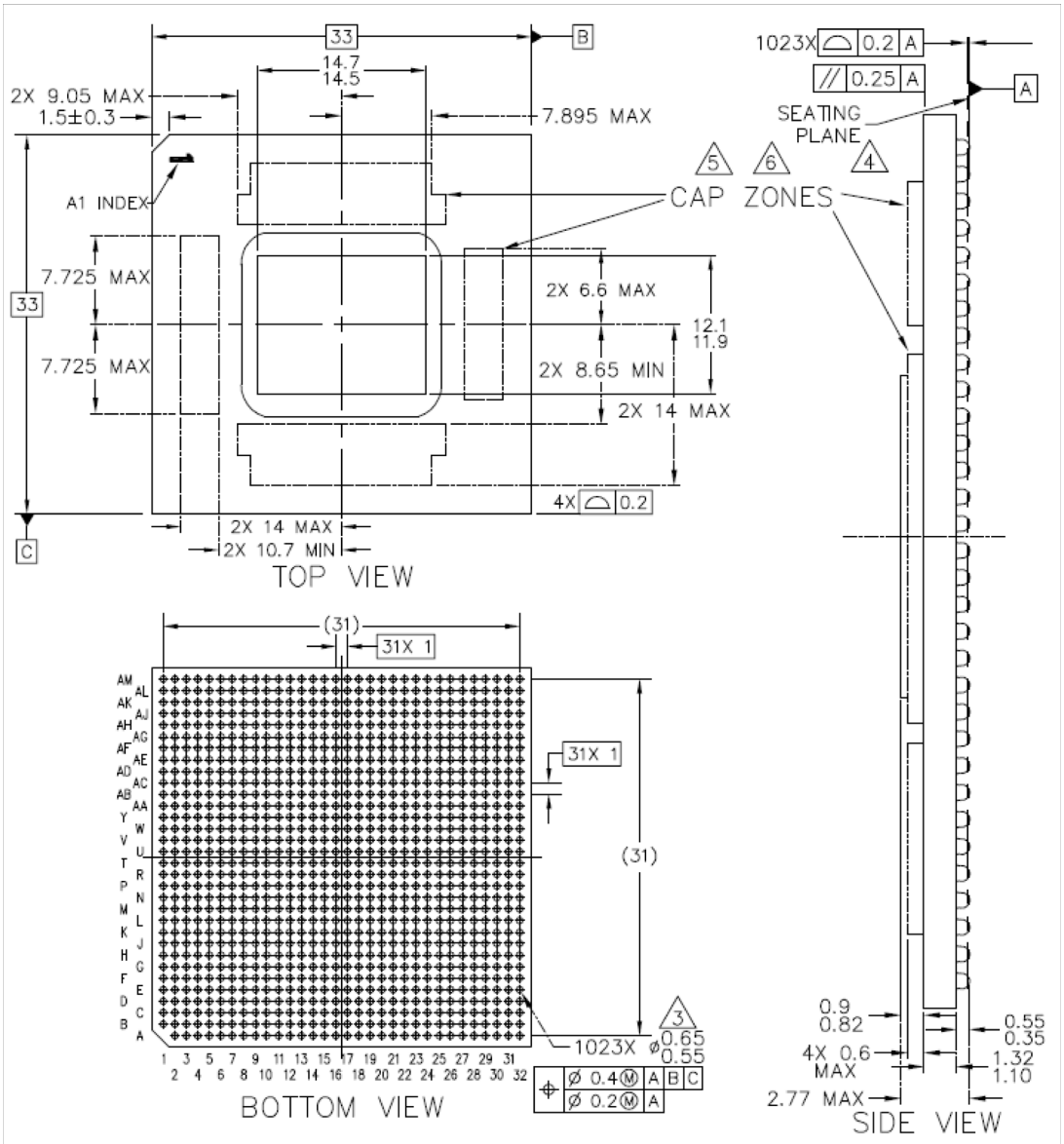

Figure 58. MPC8641D Lead-Free FC-CBGA Dimensions

NOTES for Figure 58

1. All dimensions are in millimeters.
2. Dimensions and tolerances per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is defined by the spherical crowns of the solder balls.
5. Capacitors may not be present on all devices.
6. Caution must be taken not to short capacitors or expose metal capacitor pads on package top.
7. All dimensions symmetrical about centerlines unless otherwise specified.
8. Note that for MPC8641 (single core) the solder balls for the following signals/pins are not populated in the package: VDD_Core1 (R16, R18, R20, T17, T19, T21, T23, U16, U18, U22, V17, V19, V21, V23, W16, W18, W20, W22, Y17, Y19, Y21, Y23, AA16, AA18, AA20, AA22, AB23, AC24) and SENSEVDD_Core1 (U20).

Table 63. MPC8641 Signal Reference by Functional Block (continued)

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
LCS[6]/DMA_DACK[2]	E23	O	OV_{DD}	7, 10
LCS[7]/DMA_DDONE[2]	F23	O	OV_{DD}	7, 10
LWE[0:3]/ LSDDQM[0:3]/ LBS[0:3]	E21, F21, D22, E20	O	OV_{DD}	6
LBCTL	D21	O	OV_{DD}	—
LALE	E19	O	OV_{DD}	—
LGPL0/LSDA10	F20	O	OV_{DD}	25
LGPL1/LSDWE	H20	O	OV_{DD}	25
LGPL2/LOE/ LSDRAS	J20	O	OV_{DD}	—
LGPL3/LSDCAS	K20	O	OV_{DD}	6
LGPL4/LGTA/ LUPWAIT/LPBSE	L21	I/O	OV_{DD}	42
LGPL5	J19	O	OV_{DD}	6
LCKE	H19	O	OV_{DD}	—
LCLK[0:2]	G19, L19, M20	O	OV_{DD}	—
LSYNC_IN	M19	I	OV_{DD}	—
LSYNC_OUT	D20	O	OV_{DD}	—
DMA Signals[5]				
DMA_DREQ[0:1]	E31, E32	I	OV_{DD}	—
DMA_DREQ[2]/LCS[5]	B23	I	OV_{DD}	9, 10
DMA_DREQ[3]/IRQ[9]	B30	I	OV_{DD}	10
DMA_DACK[0:1]	D32, F30	O	OV_{DD}	—
DMA_DACK[2]/LCS[6]	E23	O	OV_{DD}	10
DMA_DACK[3]/IRQ[10]	C30	O	OV_{DD}	9, 10
DMA_DDONE[0:1]	F31, F32	O	OV_{DD}	—
DMA_DDONE[2]/LCS[7]	F23	O	OV_{DD}	10
DMA_DDONE[3]/IRQ[11]	D30	O	OV_{DD}	9, 10
Programmable Interrupt Controller Signals[5]				
MCP_0	F17	I	OV_{DD}	—
MCP _1	H17	I	OV_{DD}	12, *S4*
IRQ[0:8]	G28, G29, H27, J23, M23, J27, F28, J24, L23	I	OV_{DD}	—

Table 63. MPC8641 Signal Reference by Functional Block (continued)

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
$SENSEV_{SS}$_Core0	P14	Core0 GND sensing pin	—	31
$SENSEV_{SS}$_Core1	V20	Core1 GND sensing pin	—	12, 31, *S3*
$SENSEV_{DD}$_PLAT	N18	V_{DD}_PLAT sensing pin	—	28
$SENSEV_{SS}$_PLAT	P18	Platform GND sensing pin	—	29
$D1\_GV_{DD}$	B11, B14, D10, D13, F9, F12, H8, H11, H14, K10, K13, L8, P8, R6, U8, V6, W10, Y8, AA6, AB10, AC8, AD12, AE10, AF8, AG12, AH10, AJ8, AJ14, AK12, AL10, AL16	SDRAM 1 I/O supply	$D1\_GV_{DD}$ 2.5 - DDR 1.8 DDR2	—
$D2\_GV_{DD}$	B2, B5, B8, D4, D7, E2, F6, G4, H2, J6, K4, L2, M6, N4, P2, T4, U2, W4, Y2, AB4, AC2, AD6, AE4, AF2, AG6, AH4, AJ2, AK6, AL4, AM2	SDRAM 2 I/O supply	$D2\_GV_{DD}$ 2.5 V - DDR 1.8 V - DDR2	—
OV_{DD}	B22, B25, B28, D17, D24, D27, F19, F22, F26, F29, G17, H21, H24, K19, K23, M21, AM30	DUART, Local Bus, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, JTAG, Power management, I^2C, JTAG and Miscellaneous I/O voltage	OV_{DD} 3.3 V	—
LV_{DD}	AC20, AD23, AH22	TSEC1 and TSEC2 I/O voltage	LV_{DD} 2.5/3.3 V	—
TV_{DD}	AC17, AG18, AK20	TSEC3 and TSEC4 I/O voltage	TV_{DD} 2.5/3.3 V	—
SV_{DD}	H31, J29, K28, K32, L30, M28, M31, N29, R30, T31, U29, V32, W30, Y31, AA29, AB32, AC30, AD31, AE29, AG30, AH31, AJ29, AK32, AL30, AM31	Transceiver Power Supply SerDes	SV_{DD} 1.05/1.1 V	—
XV_{DD}_SRDS1	K26, L24, M27, N25, P26, R24, R28, T27, U25, V26	Serial I/O Power Supply for SerDes Port 1	XV_{DD}_SRDS1 1.05/1.1 V	—

Table 63. MPC8641 Signal Reference by Functional Block (continued)

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
AGND_SRDS1	P30	SerDes Port 1 Ground pin for AV_{DD}_SRDS1	—	—
AGND_SRDS2	AF30	SerDes Port 2 Ground pin for AV_{DD}_SRDS2	—	—
SGND	H28, H32, J30, K31, L28, L29, M32, N30, R29, T32, U30, V31, W29,Y32 AA30, AB31, AC29, AD32, AE30, AG29, AH32, AJ30, AK31, AL29, AM32	Ground pins for SV_{DD}	—	—
XGND	K27, L25, M26, N24, P27, R25, T26, U24, V27, W25, Y28, AA24, AB27, AC25, AD28, AE26, AF27, AH28, AJ26, AK27, AL26, AM28	Ground pins for XV_{DD}_SRDS*n*	—	—
Reset Configuration Signals[20]				
TSEC1_TXD[0] / cfg_alt_boot_vec	AF25	—	LV_{DD}	—
TSEC1_TXD[1]/ cfg_platform_freq	AC23	—	LV_{DD}	21
TSEC1_TXD[2:4]/ cfg_device_id[5:7]	AG24, AG23, AE24	—	LV_{DD}	—
TSEC1_TXD[5]/ cfg_tsec1_reduce	AE23	—	LV_{DD}	—
TSEC1_TXD[6:7]/ cfg_tsec1_prtcl[0:1]	AE22, AD22	—	LV_{DD}	—
TSEC2_TXD[0:3]/ cfg_rom_loc[0:3]	AB20, AJ23, AJ22, AD19	—	LV_{DD}	—
TSEC2_TXD[4], TSEC2_TX_ER/ cfg_dram_type[0:1]	AH23, AB19	—	LV_{DD}	38
TSEC2_TXD[5]/ cfg_tsec2_reduce	AH21	—	LV_{DD}	—
TSEC2_TXD[6:7]/ cfg_tsec2_prtcl[0:1]	AG22, AG21	—	LV_{DD}	—
TSEC3_TXD[0:1]/ cfg_spare[0:1]	AL21, AJ21	O	TV_{DD}	33
TSEC3_TXD[2]/ cfg_core1_enable	AM20	O	TV_{DD}	—
TSEC3_TXD[3]/ cfg_core1_lm_offset	AJ20	—	LV_{DD}	—
TSEC3_TXD[5]/ cfg_tsec3_reduce	AK21	—	LV_{DD}	—

Table 63. MPC8641 Signal Reference by Functional Block (continued)

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
TSEC3_TXD[6:7]/ cfg_tsec3_prtcl[0:1]	AL20, AL19	—	LV_{DD}	—
TSEC4_TXD[0:3]/ cfg_io_ports[0:3]	AC18, AC16, AD18, AD17	—	LV_{DD}	—
TSEC4_TXD[5]/ cfg_tsec4_reduce	AB18	—	LV_{DD}	—
TSEC4_TXD[6:7]/ cfg_tsec4_prtcl[0:1]	AB17, AB16	—	LV_{DD}	—
LAD[0:31]/ cfg_gpporcr[0:31]	A30, E29, C29, D28, D29, H25, B29, A29, C28, L22, M22, A28, C27, H26, G26, B27, B26, A27, E27, G25, D26, E26, G24, F27, A26, A25, C25, H23, K22, D25, F25, H22	—	OV_{DD}	—
$\overline{\text{LWE[0]}}$/ cfg_cpu_boot	E21	—	OV_{DD}	—
$\overline{\text{LWE[1]}}$/ cfg_rio_sys_size	F21	—	OV_{DD}	—
$\overline{\text{LWE[2:3]}}$/ cfg_host_agt[0:1]	D22, E20	—	OV_{DD}	—
LDP[0:3], LA[27] / cfg_core_pll[0:4]	A24, E24, C24, B24, J21	—	OV_{DD}	22
LA[28:31]/ cfg_sys_pll[0:3]	K21, G22, F24, G21	—	OV_{DD}	22
LGPL[3], LGPL[5]/ cfg_boot_seq[0:1]	K20, J19	—	OV_{DD}	—
D1_MSRCID[0]/ cfg_mem_debug	F15	—	OV_{DD}	—
D1_MSRCID[1]/ cfg_ddr_debug	K15	—	OV_{DD}	—

18.4.1 SYSCLK to Platform Frequency Options

Table 70 shows some SYSCLK frequencies and the expected MPX frequency values based on the MPX clock to SYSCLK ratio. Note that frequencies between 400 MHz and 500 MHz are NOT supported on the platform. See note regarding *cfg_platform_freq* in Section 17, "Signal Listings," because it is a reset configuration pin that is related to platform frequency.

Table 70. Frequency Options of SYSCLK with Respect to Platform/MPX Clock Speed

MPX to SYSCLK Ratio	SYSCLK (MHz)					
	66	83	100	111	133	167
	Platform/MPX Frequency (MHz)[1]					
2						
3					400	500
4			400		533	
5			500	555		
6	400	500	600			
8	533					
9	600					

1 SYSCLK frequency range is 66-167 MHz. Platform clock/ MPX frequency range is 400 MHz, 500-600 MHz.

18.4.2 Platform to FIFO Restrictions

Please note the following FIFO maximum speed restrictions based on platform speed.

For FIFO GMII mode:

FIFO TX/RX clock frequency <= platform clock frequency/4.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 127 MHz

For FIFO encoded mode:

FIFO TX/RX clock frequency <= platform clock frequency/3.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 167 MHz

example, assuming a T_i of 30°C, a T_r of 5°C, a package $R_{\theta JC}$ = 0.1, and a typical power consumption (P_d) of 43.4 W, the following expression for T_j is obtained:

Die-junction temperature: $T_j = 30°C + 5°C + (0.1°C/W + 0.2°C/W + \theta_{sa}) \times 43.4\ W$

For this example, a $R_{\theta sa}$ value of 1.32 °C/W or less is required to maintain the die junction temperature below the maximum value of Table 2.

Though the die junction-to-ambient and the heat sink-to-ambient thermal resistances are a common figure-of-merit used for comparing the thermal performance of various microelectronic packaging technologies, one should exercise caution when only using this metric in determining thermal management because no single parameter can adequately describe three-dimensional heat flow. The final die-junction operating temperature is not only a function of the component-level thermal resistance, but the system-level design and its operating conditions. In addition to the component's power consumption, a number of factors affect the final operating die-junction temperature—airflow, board population (local heat flux of adjacent components), heat sink efficiency, heat sink placement, next-level interconnect technology, system air temperature rise, altitude, and so on.

Due to the complexity and variety of system-level boundary conditions for today's microelectronic equipment, the combined effects of the heat transfer mechanisms (radiation, convection, and conduction) may vary widely. For these reasons, we recommend using conjugate heat transfer models for the board as well as system-level designs.

For system thermal modeling, the MPC8641 thermal model is shown in Figure 62. Four cuboids are used to represent this device. The die is modeled as 12.4x15.3 mm at a thickness of 0.86 mm. See Section 3, "Power Characteristics" for power dissipation details. The substrate is modeled as a single block 33x33x1.2 mm with orthotropic conductivity: 13.5 W/(m • K) in the xy-plane and 5.3 W/(m • K) in the z-direction. The die is centered on the substrate. The bump/underfill layer is modeled as a collapsed thermal resistance between the die and substrate with a conductivity of 5.3 W/(m • K) in the thickness dimension of 0.07 mm. Because the bump/underfill is modeled with zero physical dimension (collapsed height), the die thickness was slightly enlarged to provide the correct height. The C5 solder layer is modeled as a cuboid with dimensions 33x33x0.4 mm and orthotropic thermal conductivity of 0.034 W/(m • K) in the xy-plane and 9.6 W/(m • K) in the z-direction. An LGA solder layer would be modeled as a collapsed thermal resistance with thermal conductivity of 9.6W/(m • K) and an effective height of 0.1 mm. The thermal model uses approximate dimensions to reduce grid. Please refer to the case outline for actual dimensions.

designer place at least one decoupling capacitor at each OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT pin of the device. These decoupling capacitors should receive their power from separate OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT and GND power planes in the PCB, utilizing short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT planes, to enable quick recharging of the smaller chip capacitors. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON).

20.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power (SV_{DD} and XV_{DD}_SRDS*n*) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors should be used to minimize inductance. Connections from all capacitors to power and ground should be done with multiple vias to further reduce inductance.

- First, the board should have at least 10 x 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the device. Where the board has blind vias, these capacitors should be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors should be placed in a ring around the device as close to the supply and ground connections as possible.
- Second, there should be a 1-µF ceramic chip capacitor on each side of the device. This should be done for all SerDes supplies.
- Third, between the device and any SerDes voltage regulator there should be a 10-µF, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100-µF, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

20.5 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. In general all unused active low inputs should be tied to OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT, XV_{DD}_SRDS*n*, and SV_{DD} as required and unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Special cases:

DDR - If one of the DDR ports is not being used the power supply pins for that port can be connected to ground so that there is no need to connect the individual unused inputs of that port to ground. Note that these power supplies can only be powered up again at reset for functionality to occur on the DDR port. Power supplies for other functional buses should remain powered.